

MJE172 MJE182

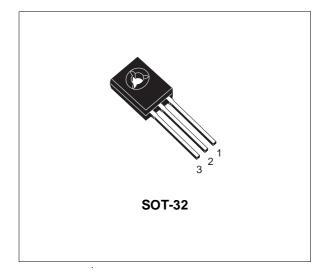
COMPLEMENTARY SILICON POWER TRANSISTORS

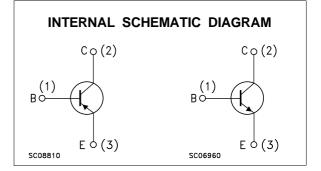
SGS-THOMSON PREFERRED SALESTYPES

COMPLEMENTARY PNP - NPN DEVICES

DESCRIPTION

The MJE172 (PNP type) and MJE182 (NPN type) are silicon epitaxial planar, complementary transistors in Jedec SOT-32 plastic package, they are designed for low power audio amplifier and low current, high speed switching applications.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit	
		NPN	MJE182		
		PNP	MJE172		
V _{CEO}	Collector-Emitter Voltage $(I_B = 0)$	80	80	V	
Vсво	Collector-Base Voltage $(I_E = 0)$	100	100	V	
V _{EBO}	Base-Emitter Voltage (I _C = 0)	7	7	V	
lc	Collector Current	3	3	А	
Ісм	Collector Peak Current	6	6	А	
IB	Base Current	1	1	А	
Ptot	Total Power Dissipation at $T_{case} \le 25 \ ^{\circ}C$	12.5	12.5	W	

THERMAL DATA

R _{thj} -amb	Thermal Resistance Junction-ambient Thermal Resistance Junction-case	Max Max	83.4	°C/W °C/W
Rthj-case		Wax	10	0/11

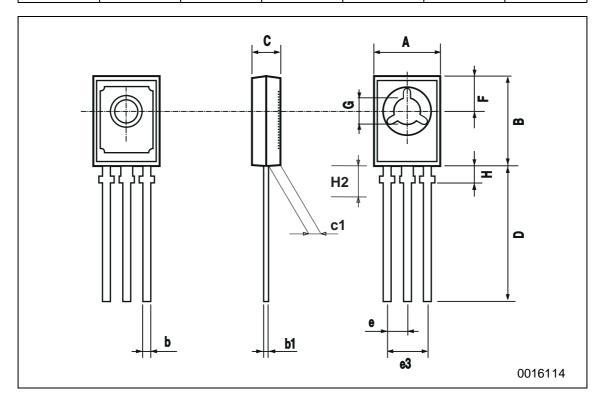
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Cond	itions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	V _{CB} = rated V _{CBO} T _{CASE} = 150 ^o C				0.1 0.1	μA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 7 V				0.1	μA
$V_{CEO(sus)^*}$	Collector-Emitter Sustaining Voltage	I _C = 10 mA		80			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{C} = 0.5 A$ $I_{C} = 1.5 A$ $I_{C} = 3 A$	I _B = 50 mA I _B = 0.15 A I _B = 0.6 A			0.3 0.9 1.7	V V V
V _{BE(sat)} *	Base-Emitter on Voltage	Ic = 1.5 A Ic = 3 A	I _B = 0.15 A I _B = 0.6 A			1.5 2	V
$V_{BE}*$	Base-Emitter on Voltage	I _C = 0.5 A	$V_{CE} = 1 V$			1.2	V
h _{FE}	DC Current Gain	$I_{C} = 0.1 A$ $I_{C} = 0.5 A$ $I_{C} = 1.5 A$	$V_{CE} = 1 V$ $V_{CE} = 1 V$ $V_{CE} = 1 V$	50 30 12		250	
f _T	Transistor Frequency	I _C = 0.1 A f = 10 MHz	V _{CE} = 10 V	50			MHz
C _{CBO}	Collector-base Capacitance	$V_{CB} = 10 V$ $I_E = 0$ for MJE172 for MJE182	f = 0.1MHz			60 40	pF pF

* Pulsed: Pulse duration = 300μ s, duty cycle $\leq 1.5\%$ For PNP type voltage and current values are negative.

57

	S	OT-32 (TO-1	26) MECHA	NICAL DA	ТА	
DIM.		mm			inch	
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
е		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	



57

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57